

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3258

HIGH CURRENT SWITCHING APPLICATIONS.

FEATURES:

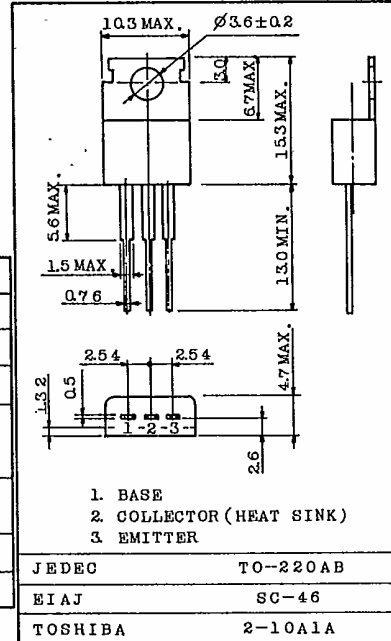
- Low Collector Saturation Voltage : $V_{CE(sat)}=0.4V(\text{Max.})$ at $I_C=3A$
- High Speed Switching Time : $t_{stg}=1.0\mu s(\text{Typ.})$
- Complementary to 2SA1293.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	7	V
Collector Current	DC I _C	5	A
	Pulse I _{CP}	8	
Collector Power Dissipation (T _c =25°C)	P _C	30	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C

INDUSTRIAL APPLICATIONS

Unit in mm



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Mounting Kit No. AC75

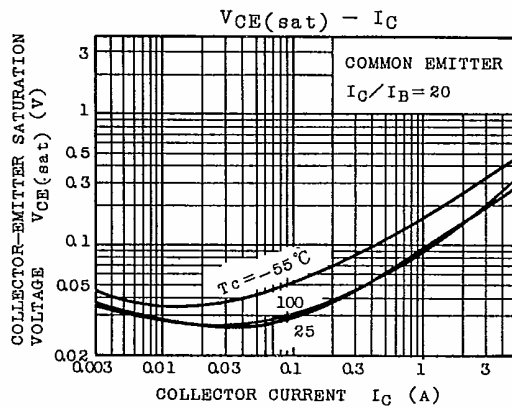
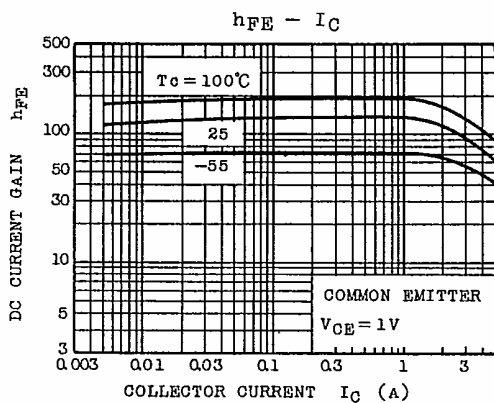
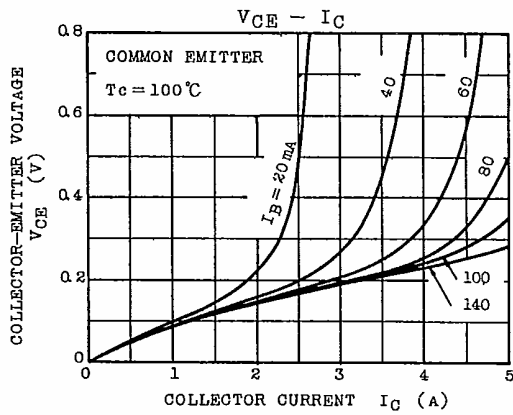
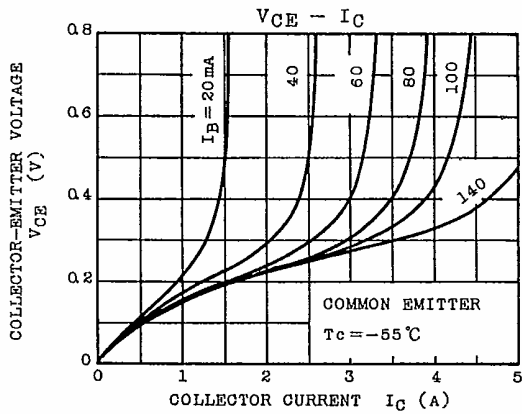
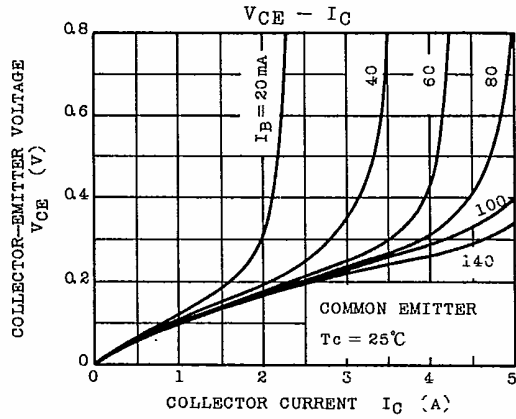
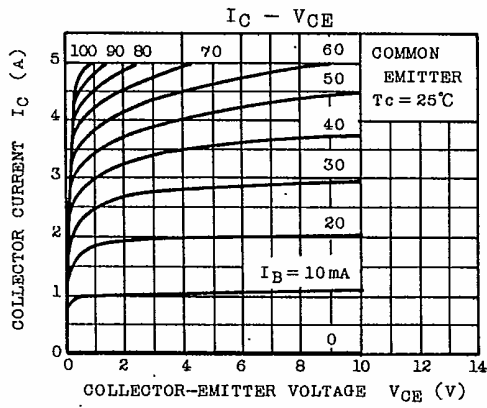
Weight : 1.9g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =100V, I _E =0	-	-	1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =7V, I _C =0	-	-	1	μA
Collector-Emitter Breakdown Voltage	V(BR) _{CEO}	I _C =10mA, I _B =0	80	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =1V, I _C =1A	70	-	240	
	h _{FE} (2)	V _{CE} =1V, I _C =3A	40	-	-	
Saturation Voltage	Collector-Emitter V _{CE(sat)}	I _C =3A, I _B =0.15A	-	0.2	0.4	V
	Base-Emitter V _{BE(sat)}		-	0.9	1.2	
Transition Frequency	f _T	V _{CE} =4V, I _C =1A	-	120	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	80	-	pF
Switching Time	Turn-on Time t _{on}		-	0.2	-	μs
	Storage Time t _{stg}		-	1.0	-	
	Fall Time t _f		-	0.1	-	

Note : h_{FE}(1) Classification O : 70~140, Y : 120~240

TOSHIBA CORPORATION

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